

600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor 13 March 2015 **Product data sheet**

1. **General description**

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9560Z

2. **Features and benefits**

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability
- High collector current gain h_{FE} at high I_C •
- AEC-Q101 gualified •

Applications 3.

- Electronic ballast for fluorescent lighting
- LED driver for LED chain module •
- LCD backlighting •
- High Intensity Discharge (HID) front lighting •
- Automotive motor management
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

Quick reference data 4.

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	600	V
I _C	collector current		-	-	0.5	А
h _{FE}	DC current gain	V_{CE} = 10 V; I _C = 50 mA; T _{amb} = 25 °C	70	135	-	





5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2, 4
2	С	collector		1
3	E	emitter		· •
4	С	collector	☐1 ☐2 ☐ 3 SC-73 (SOT223)	3 sym016

6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
PBHV8560Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PBHV8560Z	HV856Z

Limiting values 8.

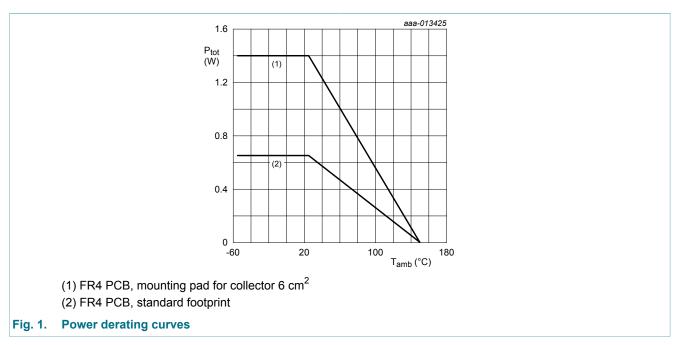
Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{CBO}	collector-base voltage	open emitter		-	600	V
V _{CEO}	collector-emitter voltage	open base		-	600	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	600	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	0.5	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1.4	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. [1] [2]

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

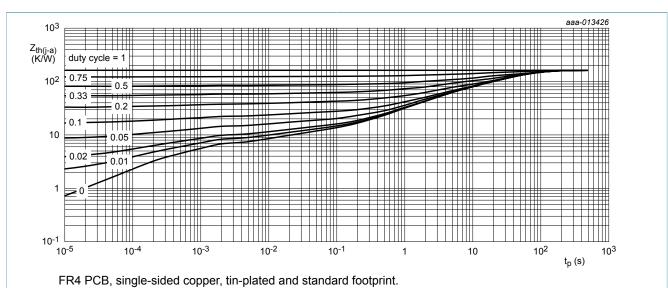


9. Thermal characteristics

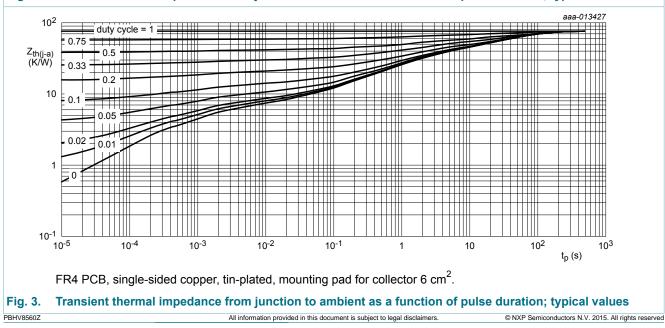
Table 6. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	-	190	K/W	
	-		[2]	-	-	89	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².





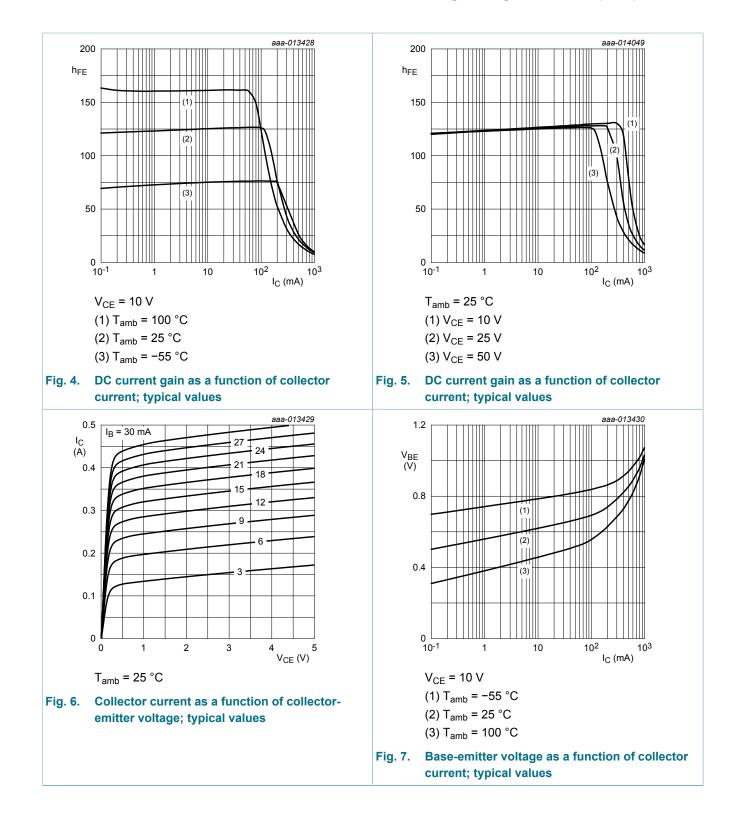


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10. Characteristics

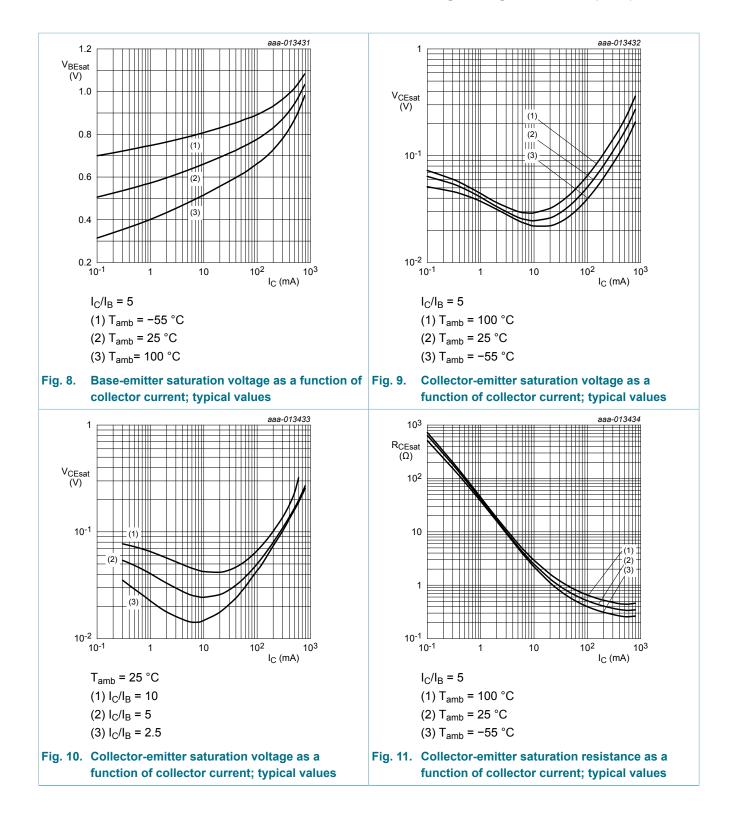
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 400 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 400 V; I _E = 0 A; T _j = 150 °C	-	-	10	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 400 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = 4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE} D	DC current gain	V_{CE} = 10 V; I _C = 50 mA; T _{amb} = 25 °C	70	135	-	
		$V_{CE} = 10 \text{ V}; \text{ I}_{C} = 100 \text{ mA}; \text{t}_{p} \le 300 \mu\text{s}; \\ \delta \le 0.02 ; \text{T}_{amb} = 25 ^{\circ}\text{C}$	70	135	-	
V _{CEsat}	collector-emitter	I_{C} = 50 mA; I_{B} = 5 mA; T_{amb} = 25 °C	-	50	100	mV
	saturation voltage	$\begin{split} I_C &= 100 \text{ mA}; I_B = 20 \text{ mA}; t_p \leq 300 \mu\text{s}; \\ \delta &\leq 0.02 ; T_{amb} = 25 ^\circ\text{C} \end{split}$	-	50	100	mV
V _{BEsat}	base-emitter saturation voltage	I_{C} = 50 mA; I_{B} = 5 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02 \ ; T_{amb}$ = 25 °C	-	-	950	mV
C _c	collector capacitance	V _{CB} = 20 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	7.5	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	710	-	pF

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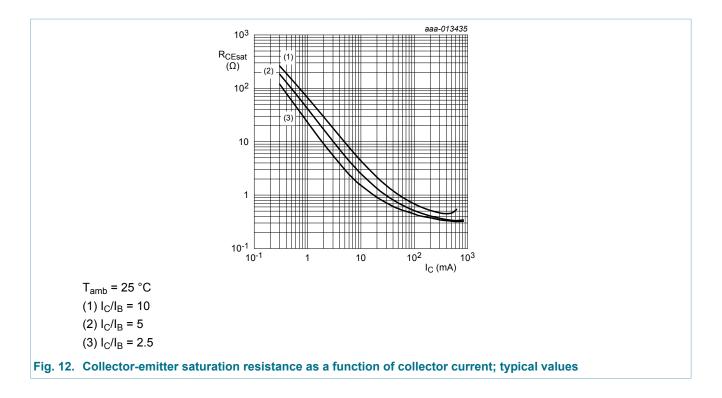
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PBHV8560Z

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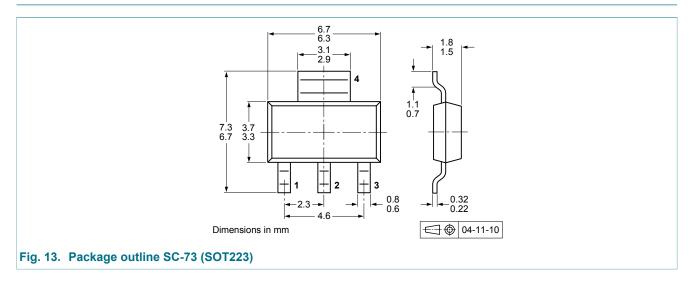


11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test gualification for discrete semiconductors, and is suitable for use in automotive applications.

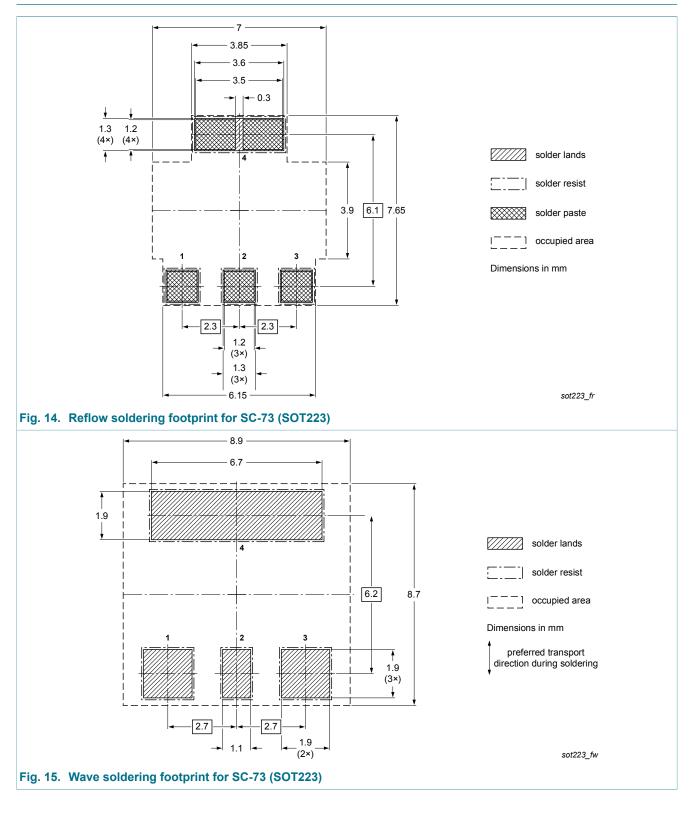
12. Package outline



Product data sheet

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13. Soldering



14. Revision history

Table 8. Revision his	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8560Z v.1	20150313	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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